

Tien-chang Lu

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ext. citations

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#	Paper	IF	Citations
308	Enhancing the output power of GaN-based LEDs grown on wet-etched patterned sapphire substrates. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 1152-1154	2.2	208
307	CW lasing of current injection blue GaN-based vertical cavity surface emitting laser. <i>Applied Physics Letters</i> , 2008 , 92, 141102	3.4	200
306	Hole injection and efficiency droop improvement in InGaN/GaN light-emitting diodes by band-engineered electron blocking layer. <i>Applied Physics Letters</i> , 2010 , 97, 261103	3.4	172
305	Low efficiency droop in blue-green m-plane InGaN/GaN light emitting diodes. <i>Applied Physics Letters</i> , 2010 , 96, 231101	3.4	136
304	Hole transport improvement in InGaN/GaN light-emitting diodes by graded-composition multiple quantum barriers. <i>Applied Physics Letters</i> , 2011 , 99, 171106	3.4	114
303	Continuous wave operation of current injected GaN vertical cavity surface emitting lasers at room temperature. <i>Applied Physics Letters</i> , 2010 , 97, 071114	3.4	109
302	Nanoscale epitaxial lateral overgrowth of GaN-based light-emitting diodes on a SiO ₂ nanorod-array patterned sapphire template. <i>Applied Physics Letters</i> , 2008 , 93, 081108	3.4	107
301	Strong light-matter interaction in ZnO microcavities. <i>Light: Science and Applications</i> , 2013 , 2, e76-e76	16.7	99
300	Study of the Excitation Power Dependent Internal Quantum Efficiency in InGaN/GaN LEDs Grown on Patterned Sapphire Substrate. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009 , 15, 1137-1143	3.8	96
299	Fabrication of InGaN/GaN nanorod light-emitting diodes with self-assembled Ni metal islands. <i>Nanotechnology</i> , 2007 , 18, 445201	3.4	89
298	Room temperature polariton lasing vs. photon lasing in a ZnO-based hybrid microcavity. <i>Optics Express</i> , 2012 , 20, 5530-7	3.3	87
297	High-Operation-Temperature Plasmonic Nanolasers on Single-Crystalline Aluminum. <i>Nano Letters</i> , 2016 , 16, 3179-86	11.5	83
296	Ultrastrong Mode Confinement in ZnO Surface Plasmon Nanolasers. <i>ACS Nano</i> , 2015 , 9, 3978-83	16.7	76
295	Enhanced light output of an InGaN/GaN light emitting diode with a nano-roughened p-GaN surface. <i>Nanotechnology</i> , 2005 , 16, 1844-1848	3.4	74
294	Temperature-Dependent Electroluminescence Efficiency in Blue InGaN/GaN Light-Emitting Diodes With Different Well Widths. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 236-238	2.2	72
293	Crack-free GaN/AlN distributed Bragg reflectors incorporated with GaN/AlN superlattices grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2006 , 88, 061904	3.4	72
292	Efficiency droop alleviation in InGaN/GaN light-emitting diodes by graded-thickness multiple quantum wells. <i>Applied Physics Letters</i> , 2010 , 97, 181101	3.4	68

291	Broadband and omnidirectional antireflection employing disordered GaN nanopillars. <i>Optics Express</i> , 2008 , 16, 8748-54	3.3	66
290	GaN-based two-dimensional surface-emitting photonic crystal lasers with AlN/GaN distributed Bragg reflector. <i>Applied Physics Letters</i> , 2008 , 92, 011129	3.4	57
289	Flexible Organometal-Halide Perovskite Lasers for Speckle Reduction in Imaging Projection. <i>ACS Nano</i> , 2019 , 13, 5421-5429	16.7	54
288	Lasing behaviors upon phase transition in solution-processed perovskite thin films. <i>Applied Physics Letters</i> , 2014 , 105, 231108	3.4	53
287	Efficiency Enhancement and Beam Shaping of GaN/InGaN Vertical-Injection Light-Emitting Diodes via High-Aspect-Ratio Nanorod Arrays. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 257-259	2.2	53
286	Fabrication and performance of blue GaN-based vertical-cavity surface emitting laser employing AlN/GaN and Ta ₂ O ₅ /BiO ₂ distributed Bragg reflector. <i>Applied Physics Letters</i> , 2005 , 87, 081105	3.4	53
285	Effects of Built-In Polarization and Carrier Overflow on InGaN Quantum-Well Lasers With Electronic Blocking Layers. <i>Journal of Lightwave Technology</i> , 2008 , 26, 329-337	4	48
284	Study on optimal growth conditions of a-plane GaN grown on r-plane sapphire by metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2007 , 300, 308-313	1.6	48
283	Single-crystalline aluminum film for ultraviolet plasmonic nanolasers. <i>Scientific Reports</i> , 2016 , 6, 19887	4.9	46
282	Enhanced light output from a nitride-based power chip of green light-emitting diodes with nano-rough surface using nanoimprint lithography. <i>Nanotechnology</i> , 2008 , 19, 185301	3.4	46
281	Optical properties of a-plane InGaN/GaN multiple quantum wells on r-plane sapphire substrates with different indium compositions. <i>Journal of Applied Physics</i> , 2009 , 105, 063105	2.5	45
280	. <i>IEEE Journal of Quantum Electronics</i> , 2006 , 42, 1196-1201	2	44
279	Ultracompact Pseudowedge Plasmonic Lasers and Laser Arrays. <i>Nano Letters</i> , 2018 , 18, 747-753	11.5	43
278	Efficiency and Droop Improvement in GaN-Based High-Voltage Light-Emitting Diodes. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1098-1100	4.4	42
277	Investigation of wavelength-dependent efficiency droop in InGaN light-emitting diodes. <i>Applied Physics B: Lasers and Optics</i> , 2010 , 98, 779-789	1.9	42
276	ZnO nanopowders fabricated by dc thermal plasma synthesis. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2006 , 134, 54-58	3.1	41
275	High output power density from GaN-based two-dimensional nanorod light-emitting diode arrays. <i>Applied Physics Letters</i> , 2009 , 94, 141111	3.4	40
274	Manipulation of nanoscale V-pits to optimize internal quantum efficiency of InGaN multiple quantum wells. <i>Applied Physics Letters</i> , 2015 , 106, 091104	3.4	39

273	Dichromatic InGaN-based white light emitting diodes by using laser lift-off and wafer-bonding schemes. <i>Applied Physics Letters</i> , 2007 , 90, 161115	3-4	38
272	Progress and prospects of GaN-based VCSEL from near UV to green emission. <i>Progress in Quantum Electronics</i> , 2018 , 57, 1-19	9-1	37
271	. <i>Journal of Display Technology</i> , 2007 , 3, 118-125		37
270	Effect of Controlled Growth Dynamics on the Microstructure of Nonpolar-Plane GaN Revealed by X-ray Diffraction. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 071002	1-4	35
269	Numerical study of optical properties of InGaN multi-quantum-well laser diodes with polarization-matched AlInGaN barrier layers. <i>Applied Physics B: Lasers and Optics</i> , 2009 , 95, 145-153	1-9	35
268	Fabrication and Characterization of GaN-Based LEDs Grown on Chemical Wet-Etched Patterned Sapphire Substrates. <i>Journal of the Electrochemical Society</i> , 2006 , 153, G1106	3-9	35
267	Enhancement of InGaN/GaN Indium-Tin Oxide Flip-Chip Light-Emitting Diodes With TiO ₂ /SiO ₂ Multilayer Stack Omnidirectional Reflector. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 2050-2052	2-2	35
266	High efficiency GaN-based light-emitting diodes with embedded air voids/SiO ₂ nanomasks. <i>Nanotechnology</i> , 2012 , 23, 045303	3-4	34
265	Large vacuum Rabi splitting in ZnO-based hybrid microcavities observed at room temperature. <i>Applied Physics Letters</i> , 2009 , 94, 061103	3-4	33
264	Room-Temperature Operation of Optically Pumped Blue-Violet GaN-Based Vertical-Cavity Surface-Emitting Lasers Fabricated by Laser Lift-Off. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 2556-2560	1-4	33
263	Structural Colors Enabled by Lattice Resonance on Silicon Nitride Metasurfaces. <i>ACS Nano</i> , 2020 , 14, 5678-5685	16-7	33
262	Reduction of Efficiency Droop in Semipolar (1 $\bar{1}$ 01) InGaN/GaN Light Emitting Diodes Grown on Patterned Silicon Substrates. <i>Applied Physics Express</i> , 2011 , 4, 012105	2-4	32
261	High density GaN/AlN quantum dots for deep UV LED with high quantum efficiency and temperature stability. <i>Scientific Reports</i> , 2014 , 4, 5166	4-9	31
260	A novel randomly textured phosphor structure for highly efficient white light-emitting diodes. <i>Nanoscale Research Letters</i> , 2012 , 7, 188	5	30
259	Characteristics of efficiency droop in GaN-based light emitting diodes with an insertion layer between the multiple quantum wells and n-GaN layer. <i>Applied Physics Letters</i> , 2010 , 97, 251114	3-4	30
258	Enhancement of Light Output Intensity by Integrating ZnO Nanorod Arrays on GaN-Based LLO Vertical LEDs. <i>Electrochemical and Solid-State Letters</i> , 2008 , 11, H84		30
257	Light Output Enhancement of Nano-Roughened GaN Laser Lift-Off Light-Emitting Diodes Formed by ICP Dry Etching. <i>IEEE Photonics Technology Letters</i> , 2007 , 19, 849-851	2-2	30
256	Room temperature current injection polariton light emitting diode with a hybrid microcavity. <i>Nano Letters</i> , 2011 , 11, 2791-5	11-5	29

255	. <i>Journal of Lightwave Technology</i> , 2008 , 26, 1455-1463	4	29
254	Dislocation reduction in GaN grown on stripe patterned r-plane sapphire substrates. <i>Applied Physics Letters</i> , 2007 , 91, 021914	3.4	29
253	Optically Pumped GaN-based Vertical Cavity Surface Emitting Lasers: Technology and Characteristics. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 5397-5407	1.4	29
252	Plasmonic Nanolasers Enhanced by Hybrid Graphene-Insulator-Metal Structures. <i>Nano Letters</i> , 2019 , 19, 5017-5024	11.5	28
251	The characteristics of the high- ϵ_r Er ₂ O ₃ (erbium oxide) dielectrics deposited on polycrystalline silicon. <i>Solid State Communications</i> , 2012 , 152, 504-508	1.6	28
250	Sub-wavelength GaN-based membrane high contrast grating reflectors. <i>Optics Express</i> , 2012 , 20, 20551-3	3.3	27
249	Phase transformation and optical characteristics of porous germanium thin film. <i>Thin Solid Films</i> , 2008 , 516, 2934-2938	2.2	27
248	Characteristics of Current-Injected GaN-Based Vertical-Cavity Surface-Emitting Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 1594-1602	3.8	26
247	Photogeneration of coherent shear phonons in orientated wurtzite semiconductors by piezoelectric coupling. <i>Physical Review B</i> , 2009 , 80,	3.3	26
246	Highly-directional emission patterns based on near single guided mode extraction from GaN-based ultrathin microcavity light-emitting diodes with photonic crystals. <i>Applied Physics Letters</i> , 2010 , 97, 013108	3.4	25
245	Optical characteristics of a-plane ZnO/Zn _{0.8} Mg _{0.2} O multiple quantum wells grown by pulsed laser deposition. <i>Journal of Applied Physics</i> , 2010 , 108, 073504	2.5	25
244	Luminance Enhancement of Flip-Chip Light-Emitting Diodes by Geometric Sapphire Shaping Structure. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 184-186	2.2	25
243	3D numerical modeling of the carrier transport and radiative efficiency for InGaN/GaN light emitting diodes with V-shaped pits. <i>AIP Advances</i> , 2016 , 6, 055208	1.5	25
242	Nanorod epitaxial lateral overgrowth of a-plane GaN with low dislocation density. <i>Applied Physics Letters</i> , 2009 , 94, 251912	3.4	24
241	Tunable light emissions from thermally evaporated In ₂ O ₃ nanostructures grown at different growth temperatures. <i>Journal of Crystal Growth</i> , 2008 , 310, 2264-2267	1.6	24
240	InGaN self-assembled quantum dots grown by metal-organic chemical vapour deposition with growth interruption. <i>Nanotechnology</i> , 2006 , 17, 1713-6	3.4	24
239	UVA light-emitting diode grown on Si substrate with enhanced electron and hole injections. <i>Optics Letters</i> , 2017 , 42, 4533-4536	3	23
238	Self-Assembled Two-Dimensional Surface Structures for Beam Shaping of GaN-Based Vertical-Injection Light-Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 12-14	2.2	23

237	Efficiency improvement of single-junction InGaP solar cells fabricated by a novel micro-hole array surface texture process. <i>Semiconductor Science and Technology</i> , 2009 , 24, 085007	1.8	23
236	Nitride-based LEDs with nano-scale textured sidewalls using natural lithography. <i>Nanotechnology</i> , 2006 , 17, 2998-3001	3.4	23
235	Effects of Different n-Electrode Patterns on Optical Characteristics of Large-Area p-Side-Down InGaN Light-Emitting Diodes Fabricated by Laser Lift-Off. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 7910-7912	1.4	23
234	Superior characteristics of microscale light emitting diodes through tightly lateral oxide-confined scheme. <i>Applied Physics Letters</i> , 2017 , 110, 021108	3.4	22
233	High-Performance Plasmonic Nanolasers with a Nanotrench Defect Cavity for Sensing Applications. <i>ACS Photonics</i> , 2018 , 5, 2638-2644	6.3	22
232	Localized surface plasmon for enhanced lasing performance in solution-processed perovskites. <i>Optics Express</i> , 2016 , 24, 20696-702	3.3	22
231	Characteristics of GaN-based photonic crystal surface emitting lasers. <i>Applied Physics Letters</i> , 2008 , 93, 111111	3.4	22
230	Development of GaN-Based Vertical-Cavity Surface-Emitting Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009 , 15, 850-860	3.8	21
229	Further Enhancement of Nitride-Based Near-Ultraviolet Vertical-Injection Light-Emitting Diodes by Adopting a Roughened Mesh-Surface. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 803-805	2.2	21
228	Optical study of a-plane InGaN/GaN multiple quantum wells with different well widths grown by metal-organic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2008 , 104, 093106	2.5	21
227	Surface roughness effects on aluminium-based ultraviolet plasmonic nanolasers. <i>Scientific Reports</i> , 2017 , 7, 39813	4.9	20
226	Improving Light Output Power of the GaN-Based Vertical-Injection Light-Emitting Diodes by Mg ⁺ Implanted Current Blocking Layer. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 688-690	2.2	20
225	. <i>Journal of Lightwave Technology</i> , 2008 , 26, 3155-3165	4	20
224	Low Droop Nonpolar GaN/InGaN Light Emitting Diode Grown on m-Plane GaN Substrate. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H501	3.9	19
223	Crystal quality improvement of a-plane GaN using epitaxial lateral overgrowth on nanorods. <i>Journal of Crystal Growth</i> , 2010 , 312, 1316-1320	1.6	19
222	Enhance light extraction of InGaN-based green LEDs by nano-imprinted 2D photonic crystal pattern. <i>Semiconductor Science and Technology</i> , 2008 , 23, 055002	1.8	19
221	Enhancement of Flip-Chip Light-Emitting Diodes With Omni-Directional Reflector and Textured Micropillar Arrays. <i>IEEE Photonics Technology Letters</i> , 2007 , 19, 1200-1202	2.2	19
220	Investigation of whispering gallery mode dependence on cavity geometry of quasiperiodic photonic crystal microcavity lasers. <i>Applied Physics Letters</i> , 2006 , 89, 231111	3.4	19

219	Emission characteristics of optically pumped GaN-based vertical-cavity surface-emitting lasers. <i>Applied Physics Letters</i> , 2006 , 89, 121112	3.4	19
218	Controllable lasing performance in solution-processed organic-inorganic hybrid perovskites. <i>Nanoscale</i> , 2016 , 8, 18483-18488	7.7	19
217	GaN-based high contrast grating surface-emitting lasers. <i>Applied Physics Letters</i> , 2013 , 102, 081111	3.4	18
216	High-Performance GaN-Based Vertical-Injection Light-Emitting Diodes With TiO ₂ /BiO ₂ Omnidirectional Reflector and n-GaN Roughness. <i>IEEE Photonics Technology Letters</i> , 2007 , 19, 565-567	2.2	18
215	Efficiency Enhancement of GaN-Based Power-Chip LEDs with Sidewall Roughness by Natural Lithography. <i>Electrochemical and Solid-State Letters</i> , 2007 , 10, H59		18
214	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 985-989	3.8	17
213	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 971-978	3.8	17
212	Strain relaxation induced microphotoluminescence characteristics of a single InGa _N -based nanopillar fabricated by focused ion beam milling. <i>Applied Physics Letters</i> , 2008 , 93, 081110	3.4	17
211	Efficiency enhancement of UV/blue light emitting diodes via nanoscaled epitaxial lateral overgrowth of GaN on a SiO ₂ nanorod-array patterned sapphire substrate. <i>Journal of Crystal Growth</i> , 2008 , 310, 5170-5174	1.6	17
210	Improved performance of GaN based light emitting diodes with ex-situ sputtered AlN nucleation layers. <i>AIP Advances</i> , 2016 , 6, 045311	1.5	17
209	High-temperature operation of GaN-based vertical-cavity surface-emitting lasers. <i>Applied Physics Express</i> , 2017 , 10, 112101	2.4	16
208	High efficiency InGa _N /GaN light emitting diodes with asymmetric triangular multiple quantum wells. <i>Applied Physics Letters</i> , 2014 , 104, 091111	3.4	16
207	Characteristics of exciton-polaritons in ZnO-based hybrid microcavities. <i>Optics Express</i> , 2011 , 19, 4101-12,3	3.3	16
206	High Q microcavity light emitting diodes with buried AlN current apertures. <i>Applied Physics Letters</i> , 2011 , 99, 041101	3.4	16
205	Growth and characterization of a-plane Al _x Ga _{1-x} N alloys by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2010 , 312, 869-873	1.6	16
204	Optical characteristics of a-plane InGa _N /GaN multiple quantum wells with different well widths. <i>Applied Physics Letters</i> , 2007 , 90, 181122	3.4	16
203	GaN-Based High- Q Vertical-Cavity Light-Emitting Diodes. <i>IEEE Electron Device Letters</i> , 2007 , 28, 884-886	3.4	16
202	Optical and Electrical Properties of GaN-Based Light Emitting Diodes Grown on Micro- and Nano-Scale Patterned Si Substrate. <i>IEEE Journal of Quantum Electronics</i> , 2011 , 47, 899-906	2	15

201	Study of InGaN/GaN Light-Emitting Diodes With Different Last Barrier Thicknesses. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 860-862	2.2	15
200	Optical properties of (1 100 1) semi-polar InGaN/GaN multiple quantum wells grown on patterned silicon substrates. <i>Journal of Crystal Growth</i> , 2011 , 318, 500-504	1.6	15
199	High-Temperature Polariton Lasing in a Strongly Coupled ZnO Microcavity. <i>Applied Physics Express</i> , 2012 , 5, 082801	2.4	15
198	Trenched epitaxial lateral overgrowth of fast coalesced a-plane GaN with low dislocation density. <i>Applied Physics Letters</i> , 2006 , 89, 251109	3.4	15
197	The lasing characteristics of GaN-based vertical-cavity surface-emitting laser with AlN-GaN and Ta ₂ O ₅ -SiO ₂ distributed Bragg reflectors. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 877-879	2.2	15
196	Quaternary AlInGaN multiple quantum well 368nm light-emitting diode. <i>Journal of Crystal Growth</i> , 2006 , 287, 582-585	1.6	15
195	Crossover from polariton lasing to exciton lasing in a strongly coupled ZnO microcavity. <i>Scientific Reports</i> , 2016 , 6, 20581	4.9	15
194	Numerical analysis on current and optical confinement of III-nitride vertical-cavity surface-emitting lasers. <i>Optics Express</i> , 2014 , 22, 9789-97	3.3	14
193	Lasing characteristics at different band edges in GaN photonic crystal surface emitting lasers. <i>Applied Physics Letters</i> , 2010 , 96, 071108	3.4	14
192	The Differences in Optical Characteristics of TiO ₂ and TiO ₂ /AAO Nanotube Arrays Fabricated by Atomic Layer Deposition. <i>Journal of the Electrochemical Society</i> , 2012 , 159, K136-K140	3.9	14
191	Magnitude-tunable sub-THz shear phonons in a non-polar GaN multiple-quantum-well p-i-n diode. <i>Applied Physics Letters</i> , 2012 , 100, 201905	3.4	14
190	Nitride-Based Thin-Film Light-Emitting Diodes With Photonic Quasi-Crystal Surface. <i>IEEE Photonics Technology Letters</i> , 2009 , 21, 331-333	2.2	14
189	Fabrication and characteristics of thin-film InGaN/GaN light-emitting diodes with TiO ₂ /SiO ₂ omnidirectional reflectors. <i>Semiconductor Science and Technology</i> , 2007 , 22, 831-835	1.8	14
188	Effect of oxygen on characteristics of nickel oxide/indium tin oxide heterojunction diodes. <i>Journal of Applied Physics</i> , 2006 , 100, 124503	2.5	14
187	Observation of strong red photoluminescence with broadband in indium oxynitride nanoparticles. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006 , 24, 1332-1335	2.9	14
186	Perfect Absorption by an Atomically Thin Crystal. <i>Physical Review Applied</i> , 2020 , 14,	4.3	14
185	Electrically Injected GaN-Based Vertical-Cavity Surface-Emitting Lasers with TiO ₂ High-Index-Contrast Grating Reflectors. <i>ACS Photonics</i> , 2020 , 7, 861-866	6.3	13
184	. <i>Journal of Lightwave Technology</i> , 2008 , 26, 1445-1454	4	13

183	Nano-roughening n-side surface of AlGaInP-based LEDs for increasing extraction efficiency. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2007 , 138, 157-160	3.1	13
182	Investigation of InGaN/GaN light emitting diodes with nano-roughened surface by excimer laser etching method. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2007 , 136, 182-186	3.1	13
181	Characteristics of a-plane GaN with the SiN _x insertion layer grown by metal-organic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2008 , 310, 4972-4975	1.6	13
180	Perovskite random lasers: a tunable coherent light source for emerging applications. <i>Nanotechnology</i> , 2021 , 32,	3.4	13
179	Low-Threshold Bound State in the Continuum Lasers in Hybrid Lattice Resonance Metasurfaces. <i>Laser and Photonics Reviews</i> , 2021 , 15, 2100118	8.3	13
178	High-Efficiency InGaN/GaN CoreShell Nanorod Light-Emitting Diodes With Low-Peak Blueshift and Efficiency Droop. <i>IEEE Nanotechnology Magazine</i> , 2017 , 16, 355-358	2.6	12
177	Threshold gain analysis in GaN-based photonic crystal surface emitting lasers. <i>Optics Letters</i> , 2011 , 36, 1908-10	3	12
176	Study of the internal quantum efficiency of InGaN/GaN UV LEDs on patterned sapphire substrate using the electroluminescence method. <i>Journal of Crystal Growth</i> , 2011 , 315, 242-245	1.6	12
175	High-Brightness InGaN/GaN Flip-Chip Light-Emitting Diodes With Triple-Light Scattering Layers. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 659-661	2.2	12
174	Enhanced Vertical Extraction Efficiency From a Thin-Film InGaN/GaN Light-Emitting Diode Using a 2-D Photonic Crystal and an Omnidirectional Reflector. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 836-838	2.2	12
173	Lasing characteristics of a GaN photonic crystal nanocavity light source. <i>Applied Physics Letters</i> , 2007 , 91, 041101	3.4	12
172	GaN-based LEDs with Al-deposited V-shaped sapphire facet mirror. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 724-726	2.2	12
171	Three dimensional characterization of GaN-based light emitting diode grown on patterned sapphire substrate by confocal Raman and photoluminescence spectromicroscopy. <i>Scientific Reports</i> , 2017 , 7, 45519	4.9	11
170	Optical characterizations and reverse-bias electroluminescence observation for reliability investigations of the InGaN light emitting diode. <i>Microelectronic Engineering</i> , 2013 , 101, 42-46	2.5	11
169	Localized Lasing Mode in GaN Quasi-Periodic Nanopillars at Room Temperature. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 4900206-4900206	3.8	11
168	Output Power Enhancement of Vertical-Injection Ultraviolet Light-Emitting Diodes by GaN-Free and Surface Roughness Structures. <i>Electrochemical and Solid-State Letters</i> , 2009 , 12, H44		11
167	Extraction Efficiency Enhancement of GaN-Based Light-Emitting Diodes by Microhole Array and Roughened Surface Oxide. <i>IEEE Electron Device Letters</i> , 2009 , 30, 496-498	4.4	11
166	High brightness GaN-based flip-chip light-emitting diodes by adopting geometric sapphire shaping structure. <i>Semiconductor Science and Technology</i> , 2008 , 23, 025015	1.8	11

- 165 Whispering gallery mode of modified octagonal quasiperiodic photonic crystal single-defect microcavity and its side-mode reduction. *Applied Physics Letters*, **2006**, 88, 201104 3.4 11
- 164 Depth-resolved confocal micro-Raman spectroscopy for characterizing GaN-based light emitting diode structures. *Review of Scientific Instruments*, **2013**, 84, 113108 1.7 10
- 163 Enhanced Light Extraction in Wafer-Bonded AlGaInP-Based Light-Emitting Diodes via Micro- and Nanoscale Surface Textured. *IEEE Electron Device Letters*, **2009**, 30, 1054-1056 4.4 10
- 162 Fabrication of Microcavity Light-Emitting Diodes Using Highly Reflective AlN/GaN and Ta₂O₅/BiO₂ Distributed Bragg Mirrors. *IEEE Photonics Technology Letters*, **2007**, 19, 999-1001 2.2 10
- 161 High-reflectivity ultraviolet AlN/AlGaIn distributed Bragg reflectors grown by metalorganic chemical vapor deposition. *Journal of Crystal Growth*, **2008**, 310, 4871-4875 1.6 10
- 160 Design and Fabrication of the Reliable GaN Based Vertical-Cavity Surface-Emitting Laser via Tunnel Junction. *Crystals*, **2019**, 9, 187 2.3 9
- 159 Study of Band-Edge Modes in GaN-Based Photonic Crystal Surface-Emitting Lasers by the Multiple-Scattering Method. *IEEE Journal of Selected Topics in Quantum Electronics*, **2012**, 18, 1629-1635 3.8 9
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